

## FDC658AP

# Single P-Channel Logic Level PowerTrench® MOSFET, -30V, -4A, 50mΩ

### Product Overview

For complete documentation, see the data sheet.

This P-Channel Logic Level MOSFET is produced using an advanced PowerTrench® process. It has been optimized for battery power management applications.

### Features

- Max  $r_{DS(on)}$  = 50 mΩ @  $V_{GS} = -10\text{ V}$ ,  $I_D = -4\text{ A}$
- Max  $r_{DS(on)}$  = 75 mΩ @  $V_{GS} = -4.5\text{ V}$ ,  $I_D = -3.4\text{ A}$
- Low Gate Charge
- High performance trench technology for extremely low  $r_{DS(on)}$
- RoHS Compliant

### Applications

- This product is general usage and suitable for many different applications.

### Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DS}^{(BR)}$ Min (V)	$V_{GS}^{Max}$ (V)	$V_{GS}^{(t)}$ Max (V)	$I_D^{Max}$ (A)	$P_D^{Max}$ (W)	$R_{DS(on)}^{Max}$ @ $V_{GS} = 2.5\text{ V}$ (mΩ)	$R_{DS(on)}^{Max}$ @ $V_{GS} = 4.5\text{ V}$ (mΩ)	$R_{DS(on)}^{Max}$ @ $V_{GS} = 10\text{ V}$ (mΩ)	$Q_g^{Typ}$ @ $V_{GS} = 4.5\text{ V}$ (nC)	$Q_g^{Typ}$ @ $V_{GS} = 10\text{ V}$ (nC)	$C_{iss}^{Typ}$ (pF)	Package Type
FDC658AP	0.1329		Active	P-Channel	Single	-30	25	-3	-4	1.6	-	75	50	4.9	6	470	TSO T-23-6